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(WDS) BUR920010128US1

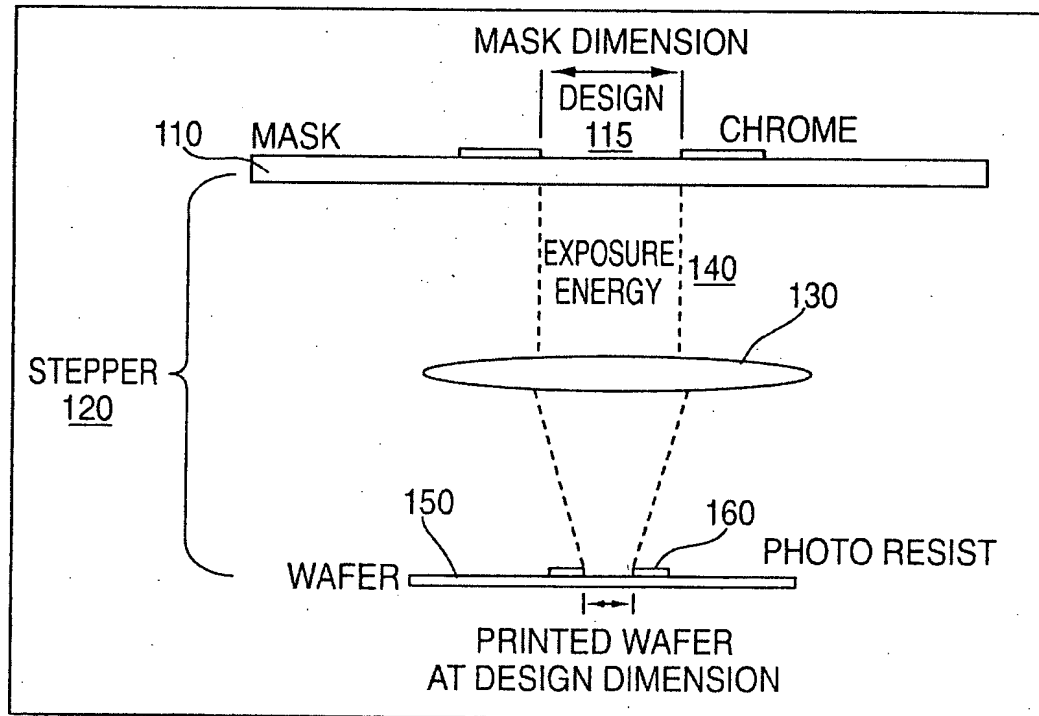


FIG. 1
PRIOR ART

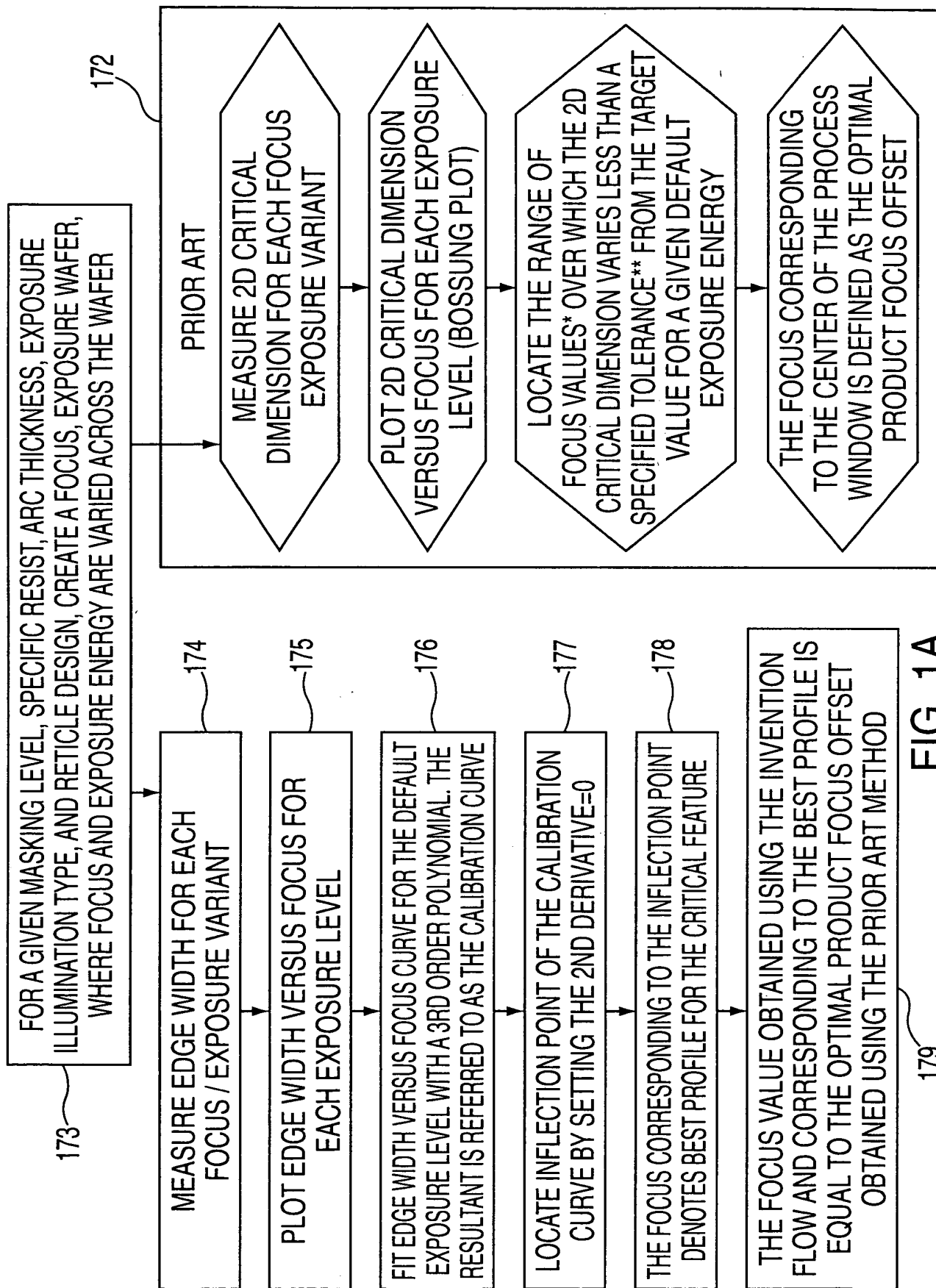


FIG. 1A



INVENTION FLOW

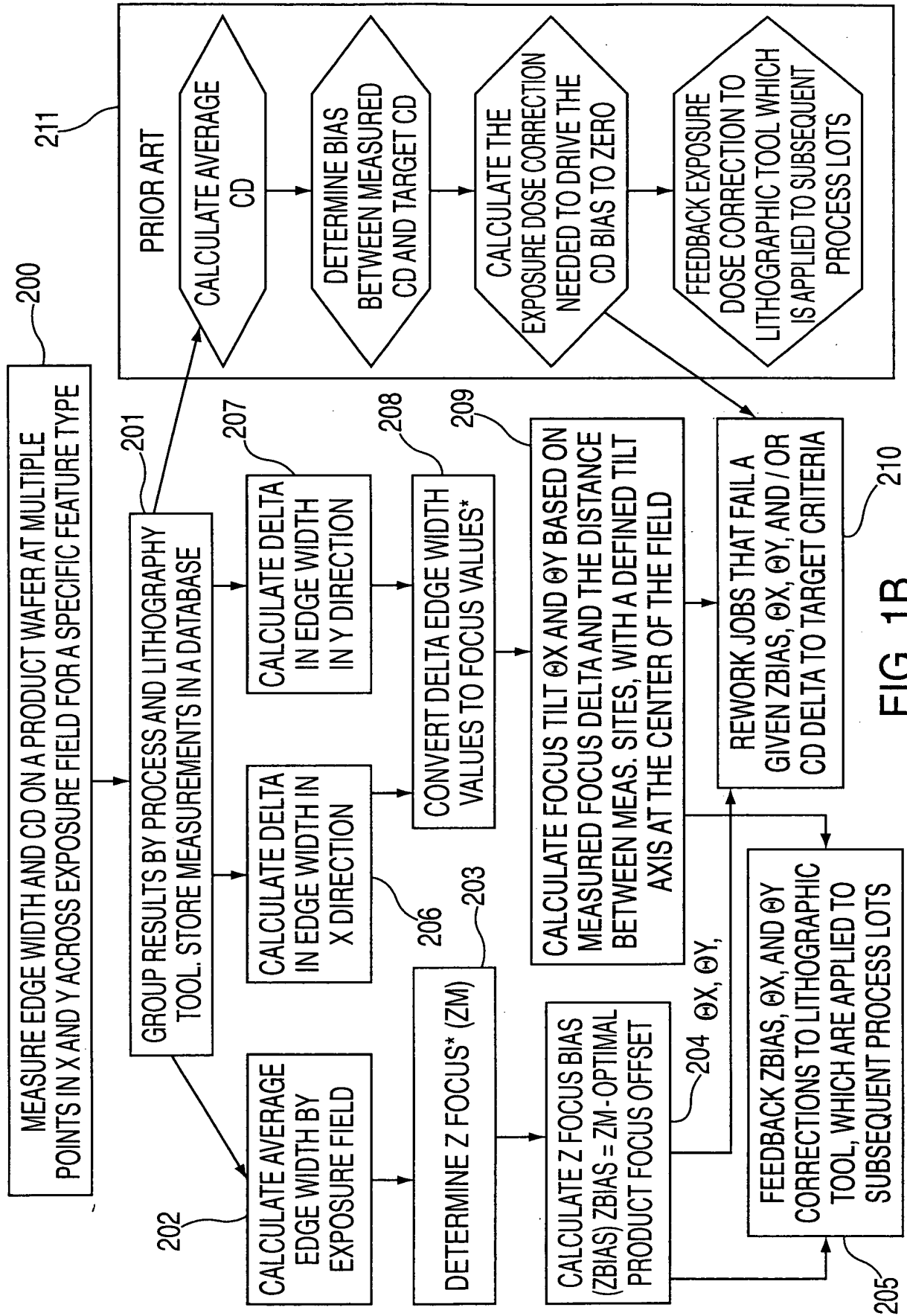
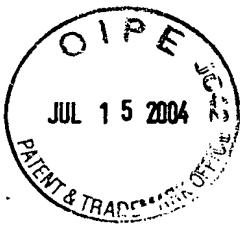


FIG. 1B



SEM WAVEFORM VS. IMAGE PROFILE

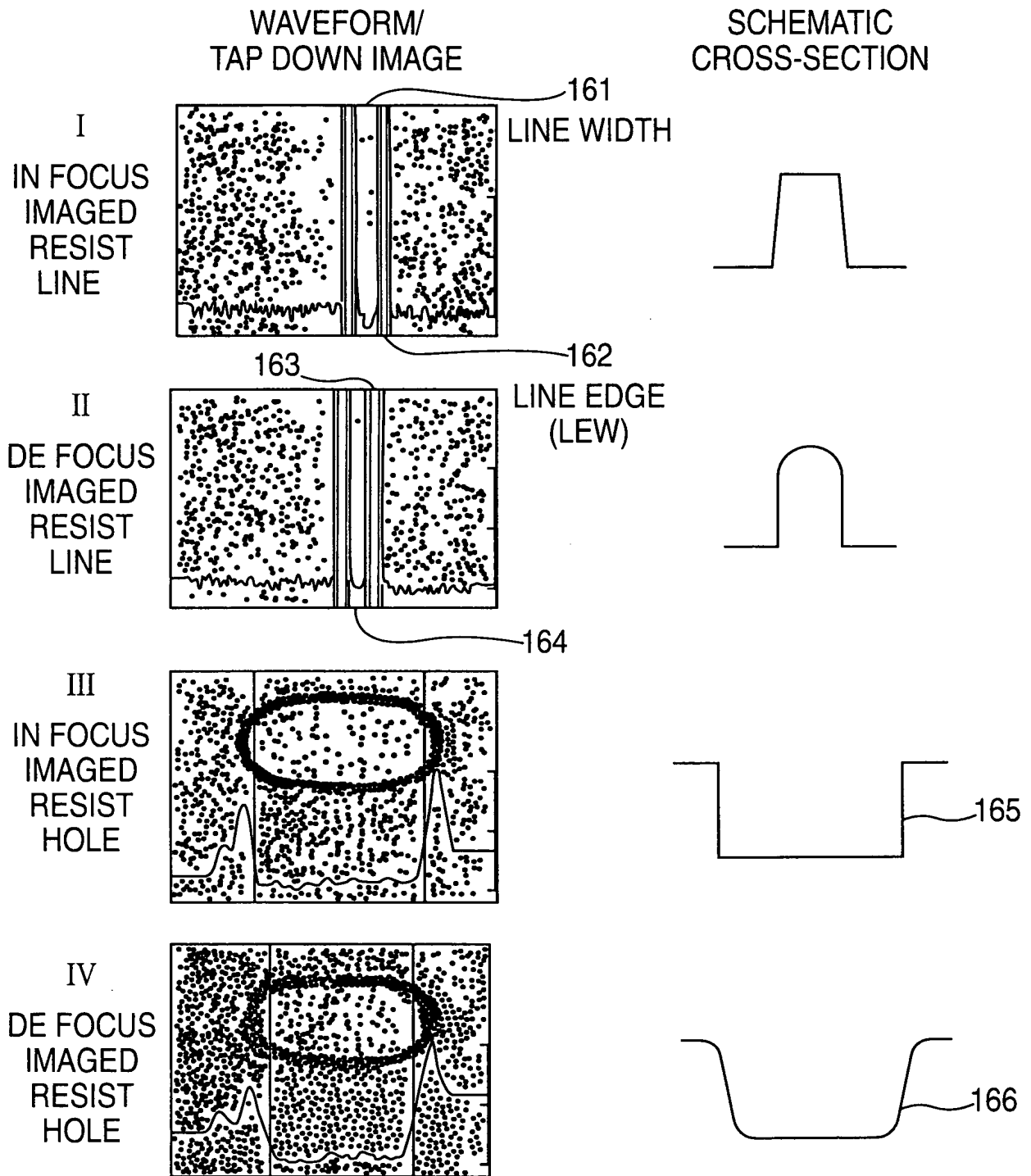


FIG. 1C

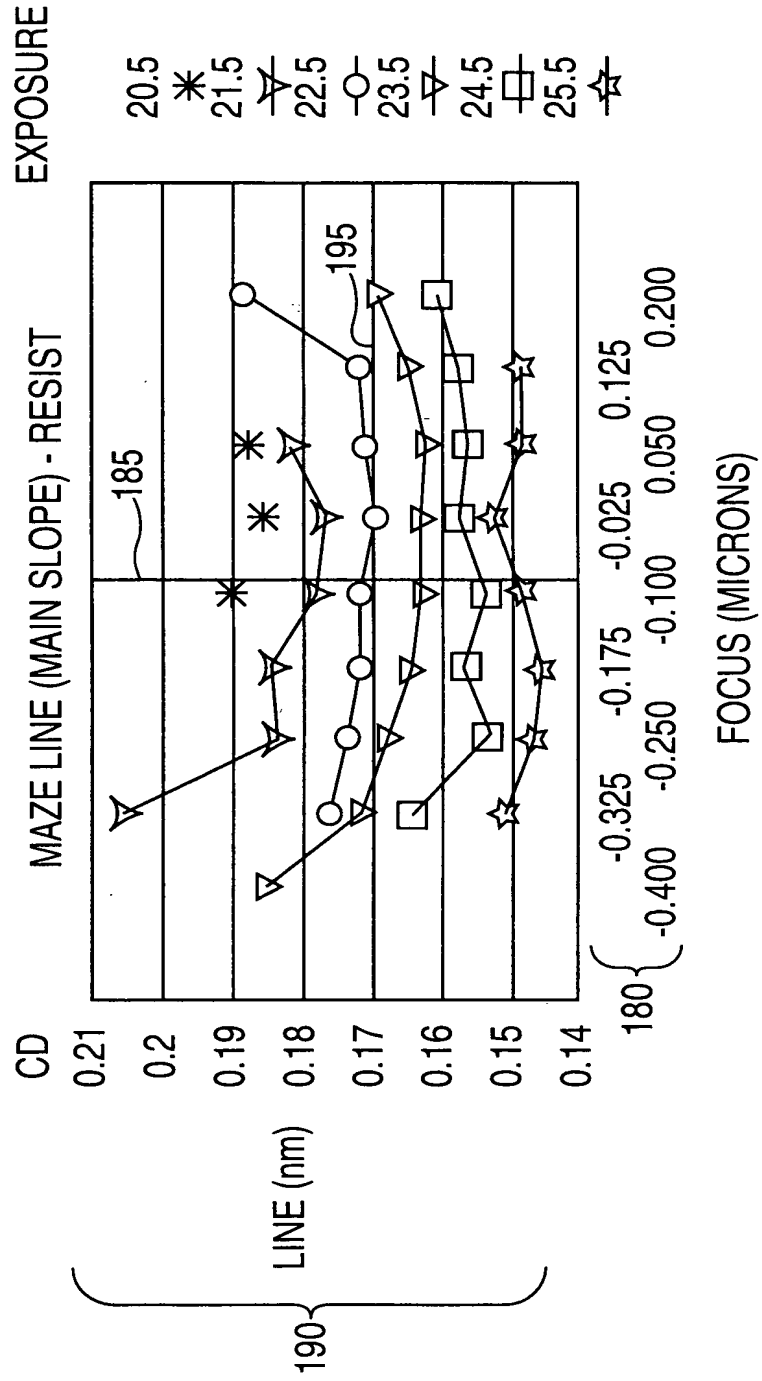
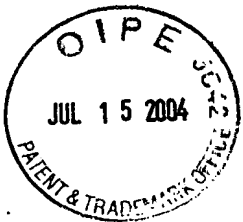


FIG. 1D



RESIST CONTACT DIMENSION CHANGE WITH FOCUS AND/OR EXPOSURE
KCELL CONTACTS (BOTTOM VIEW) - RESIST

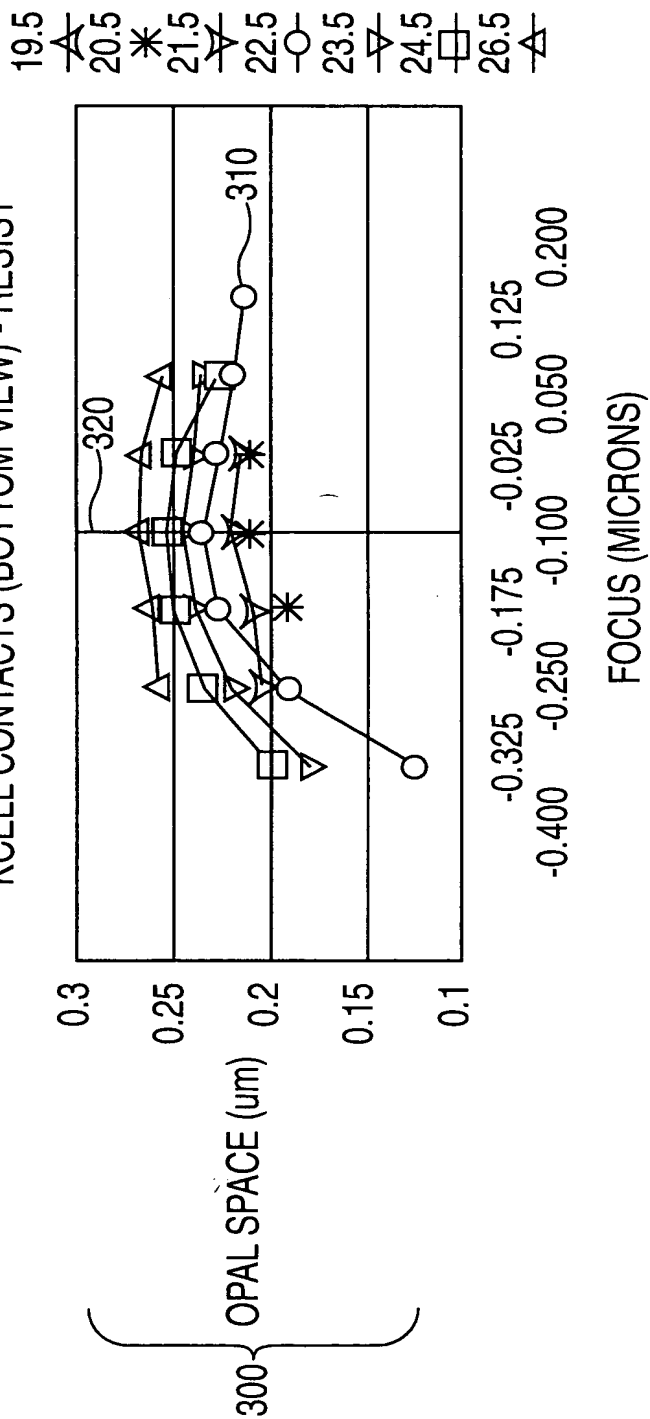


FIG. 2

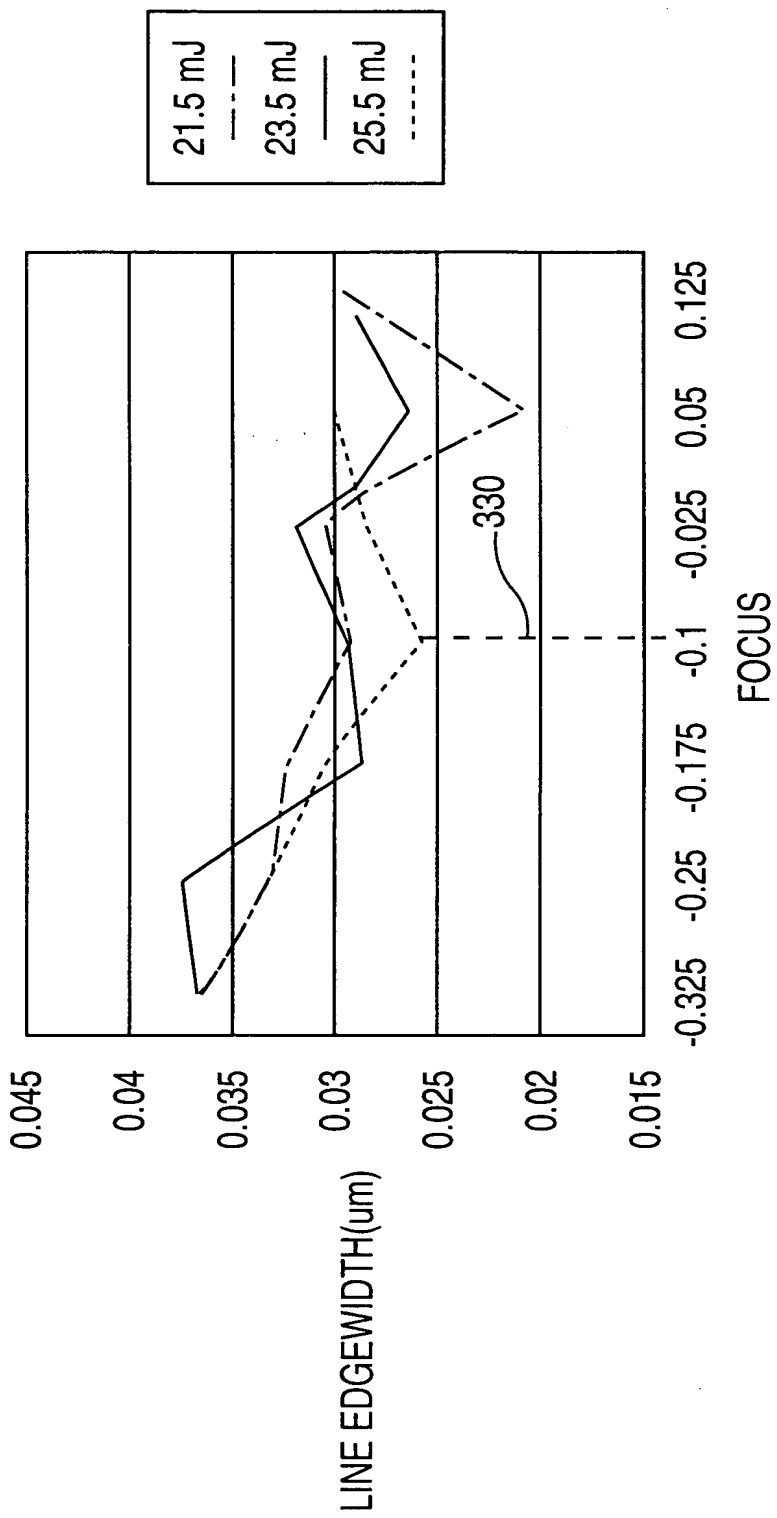


FIG. 3

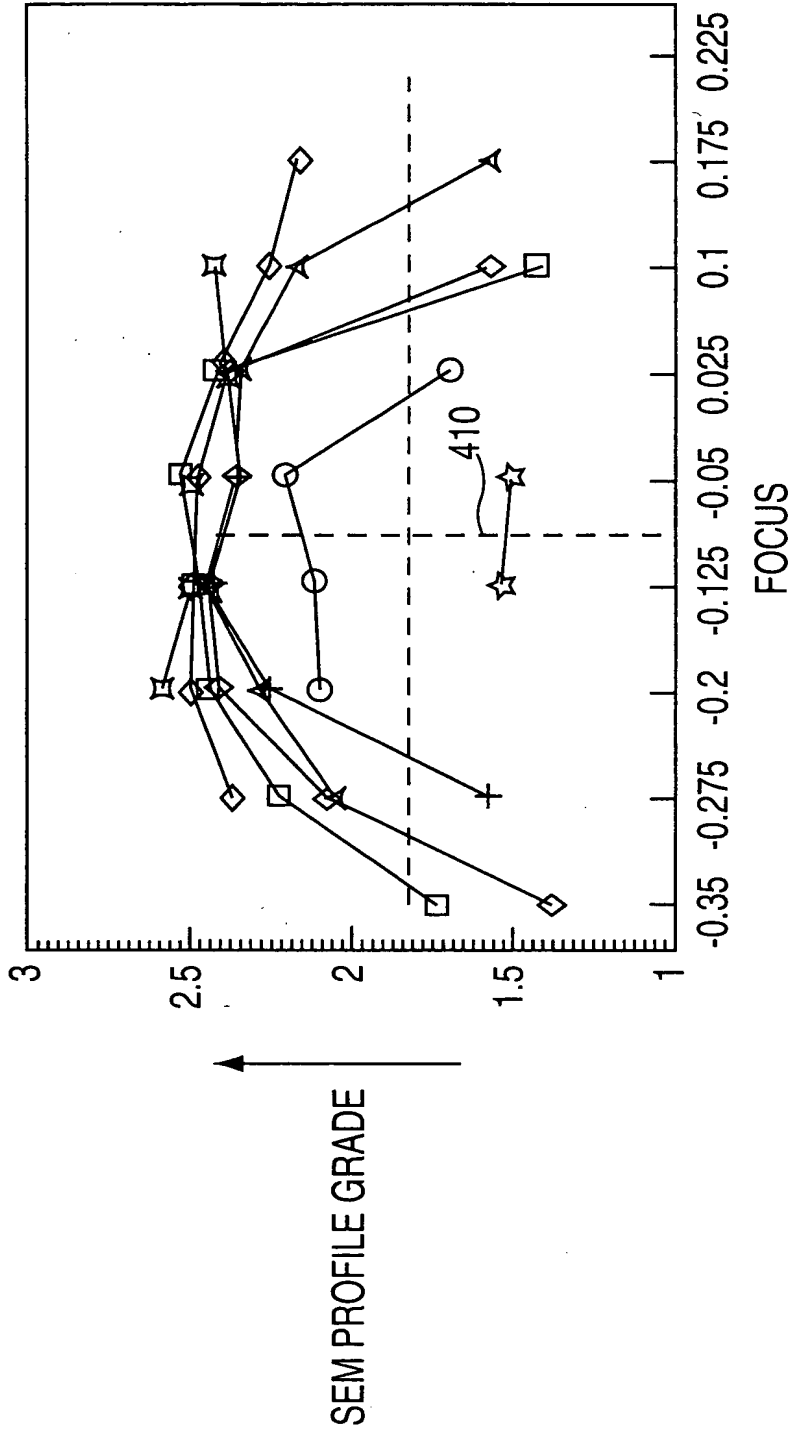


FIG. 4



CRITICAL DIMENSION OF IMAGED PHOTORESIST AS MEASURED BY CD

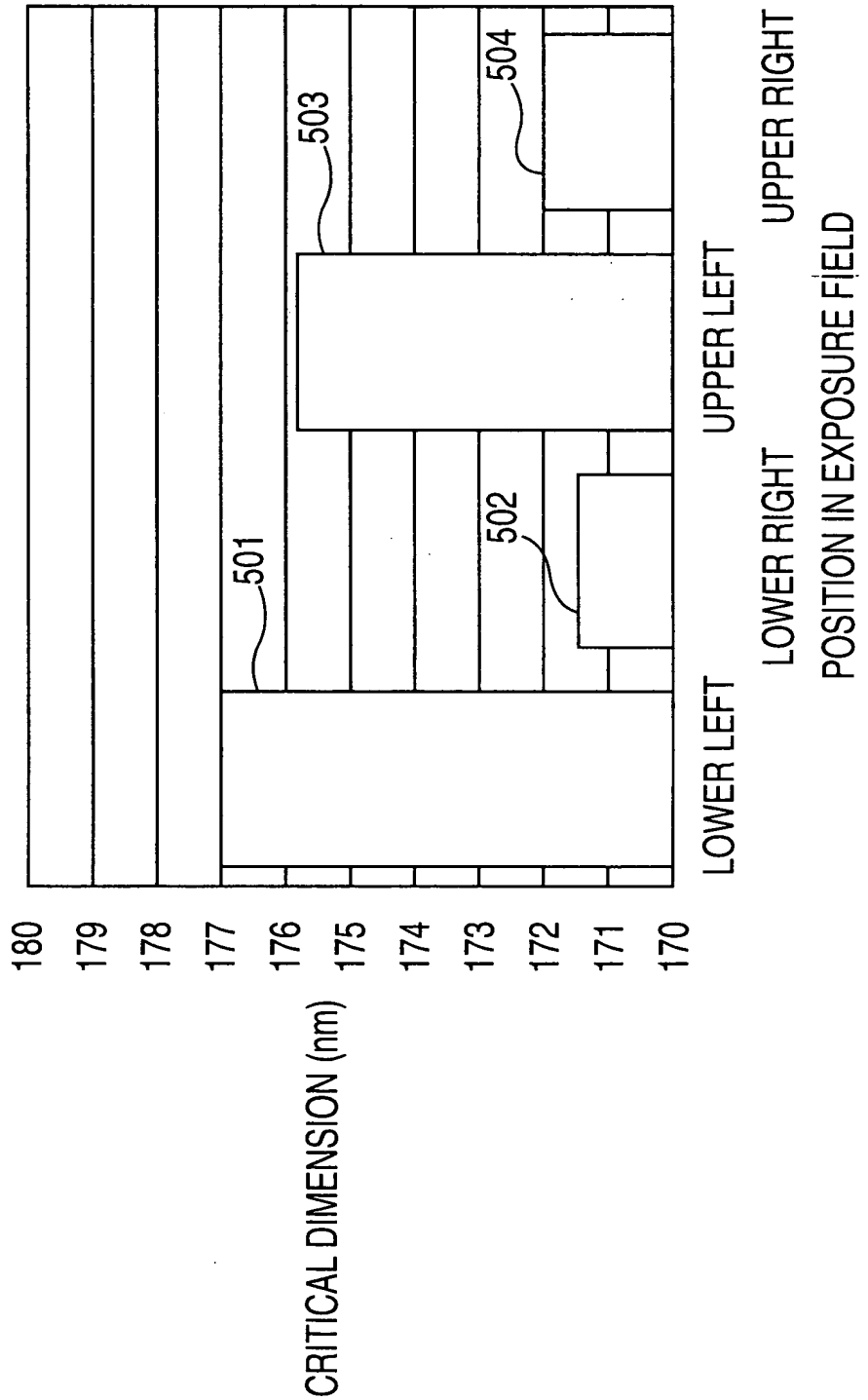
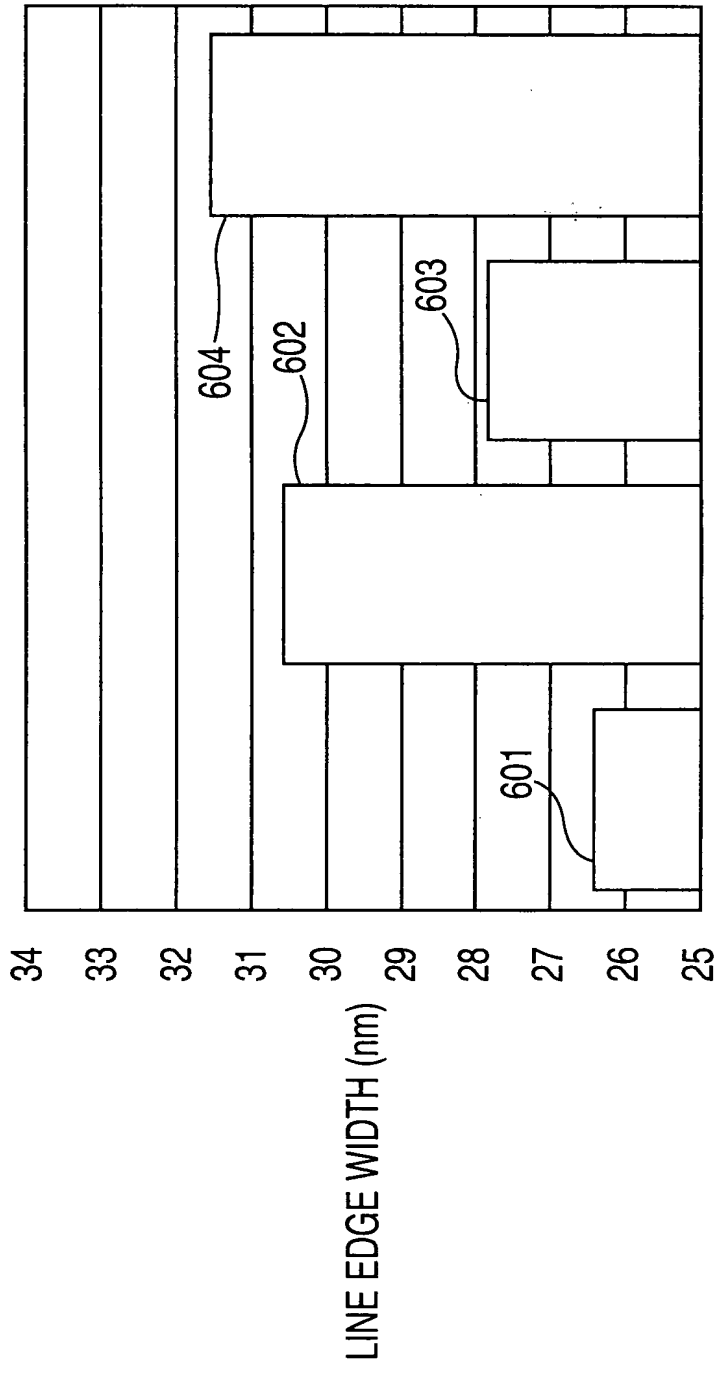


FIG. 5



LINE EDGE WIDTH OF IMAGED PHOTORESIST AS MEASURED BY CD



LOWER LEFT UPPER LEFT
LOWER RIGHT UPPER RIGHT
POSITION IN EXPOSURE FIELD

FIG. 6



X/Y TILT DETERMINATION USING EDGE WIDTH MEASUREMENT

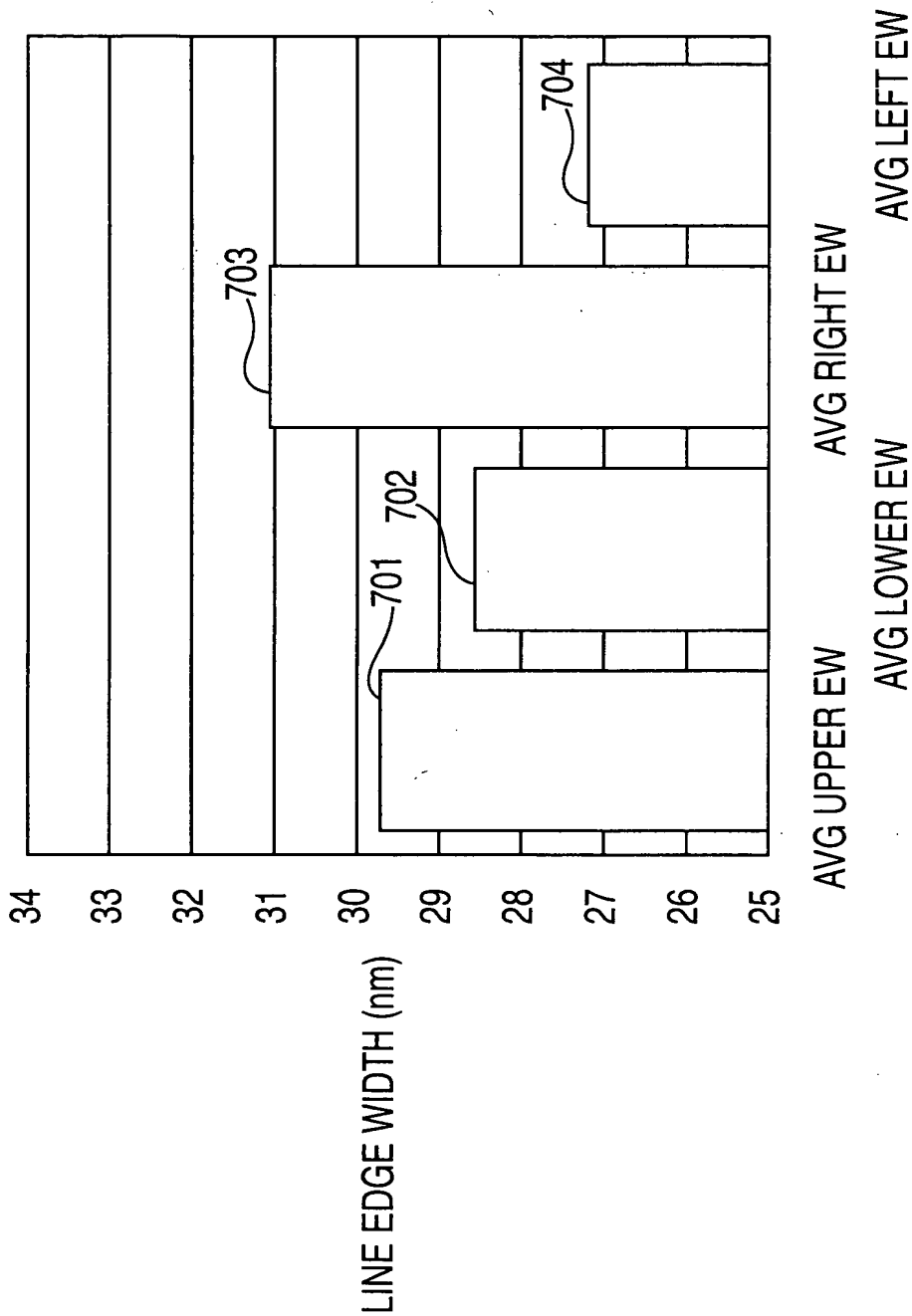


FIG. 7

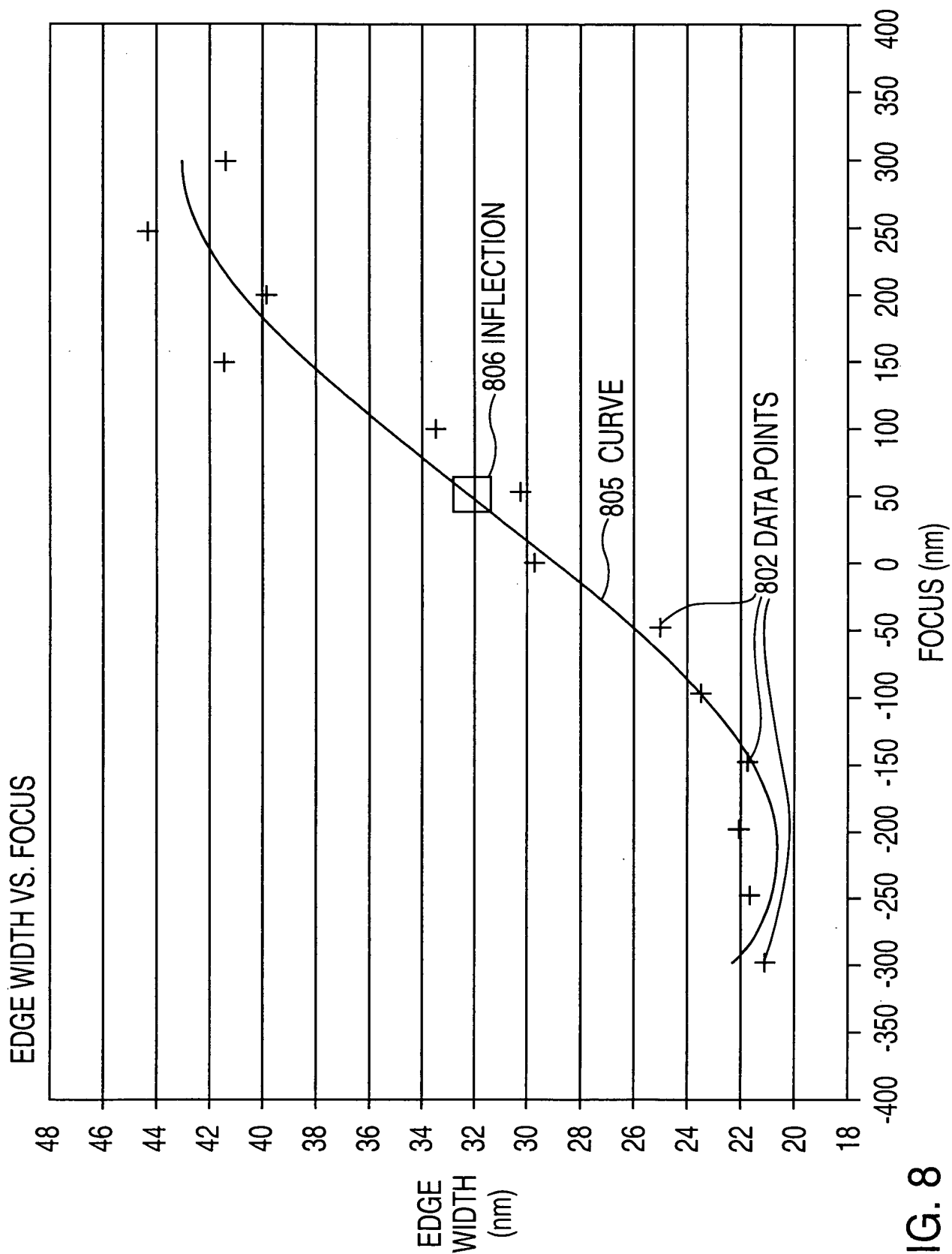


FIG. 8



XY TILT DETERMINATION USING EDGE WIDTH MEASUREMENT

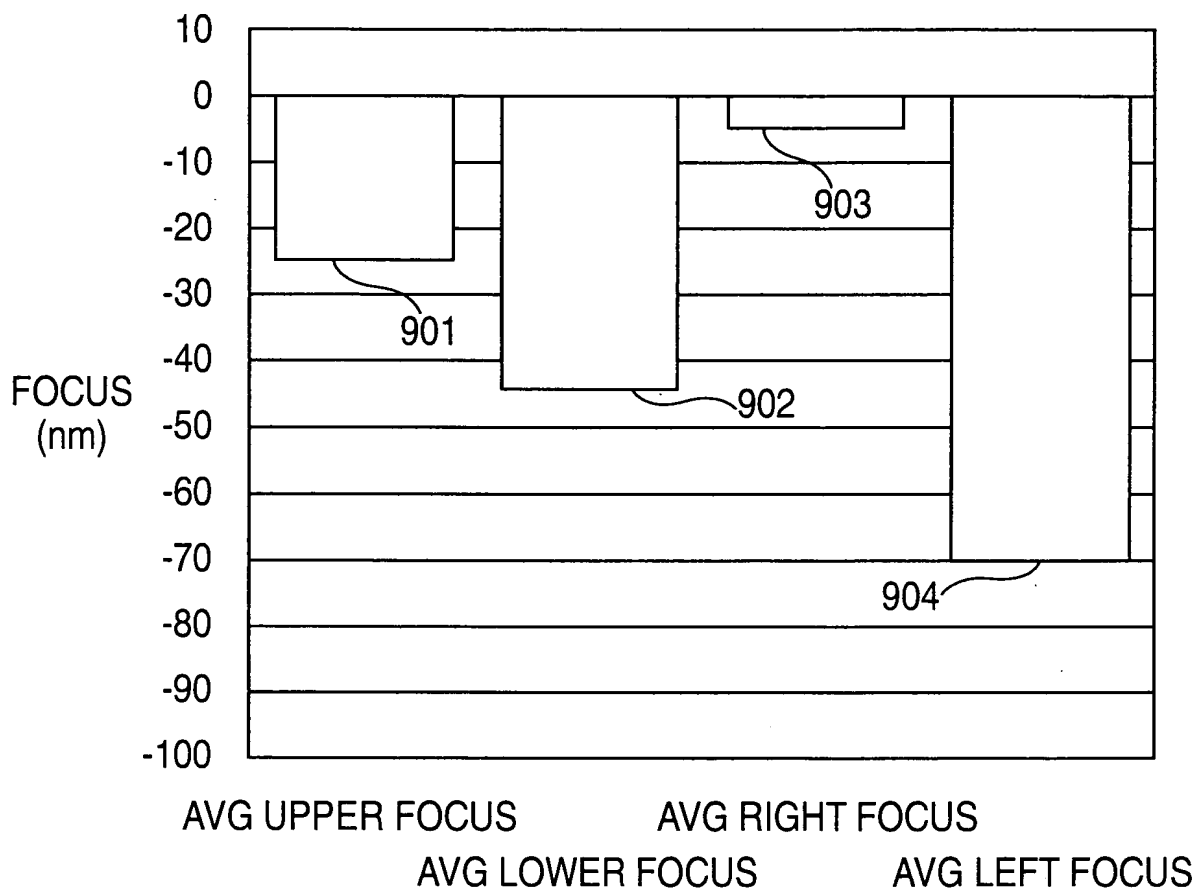


FIG. 9

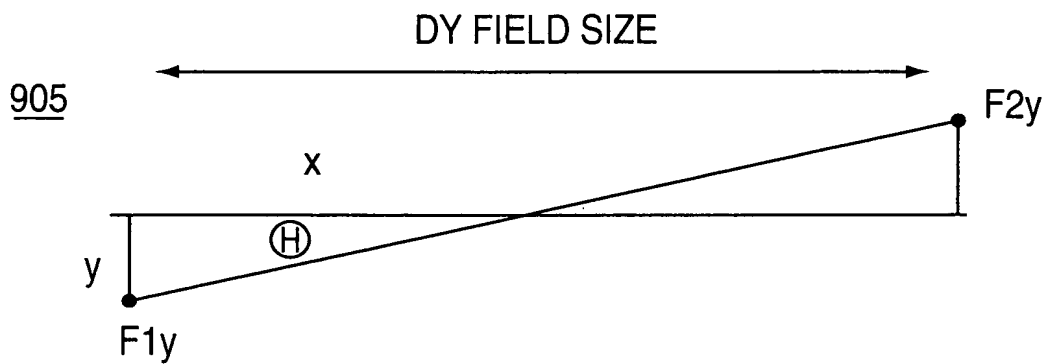
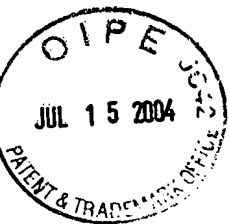


FIG. 10

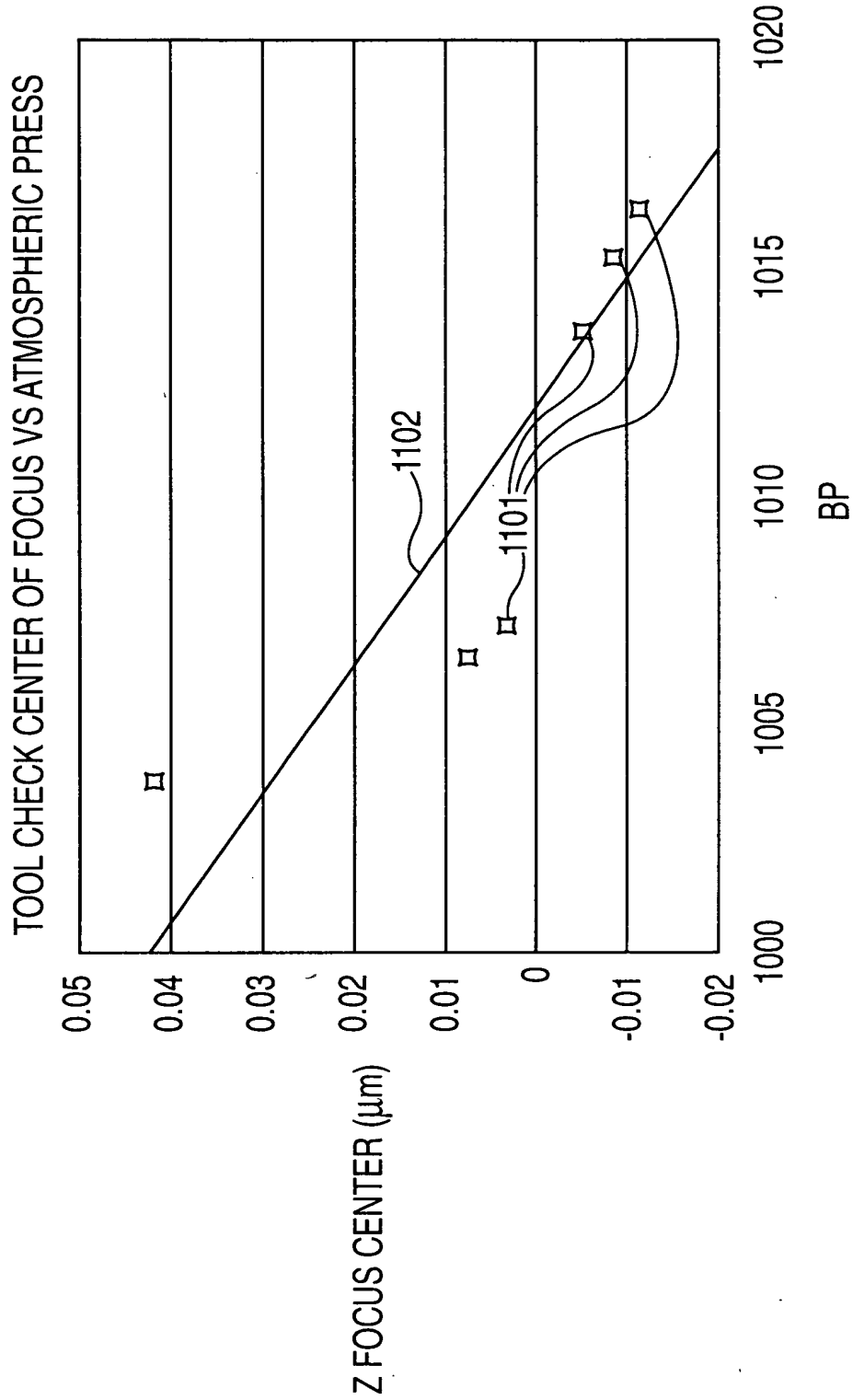


FIG. 11

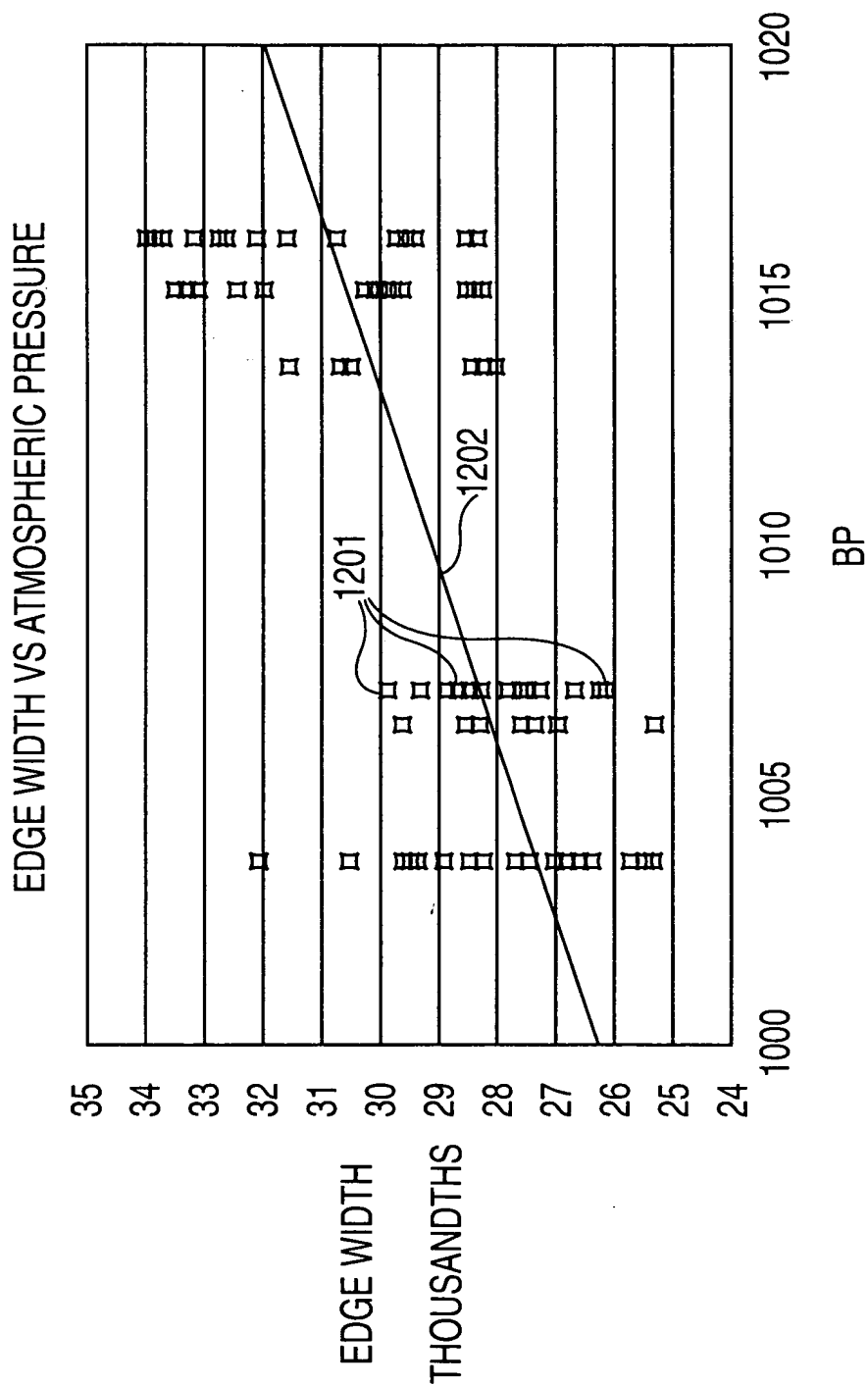


FIG. 12



TABLE OF RUN RULES

<u>1310</u> TOOL	<u>1320</u> TECHNOLOGY	<u>1330</u> WAFERPN	<u>1340</u> PROCESS	<u>1350</u> OPT	<u>1360</u> DEFAULT EXPOSURE	<u>1370</u> FOCUS
U82V	ICE8S3D	*	MC	F	19.00	0.10
U82V	ICEC8S2	*	MC	F	19.00	0.10
U82V	ICEC8S3	*	MC	F	19.00	0.10
U84V	CMOS6X1	*	MC	F	20.00	0.00
U86V	CSO19S0	*	MC9S	F	24.00	-0.10
U86V	CSO19S0	0000008J0640	MC9S	F	30.00	-0.10
U86V	CSO19S0	0000008J0645	MC9S	F	30.00	-0.10
U86V	CSO19S0	0000057P6438	MC9S	F	28.00	-0.05
U86V	CSO19S2	*	MC9S	F	25.00	-0.10
U92V	CSO19S0	*	MC9S	F	24	-0.10
U92V	CSO19S0	0000008J0639	MC9S	F	30.00	-0.10
U92V	CSO19S0	0000008J0640	MC9S	F	30.00	-0.10

FIG. 13
(PRIOR ART)

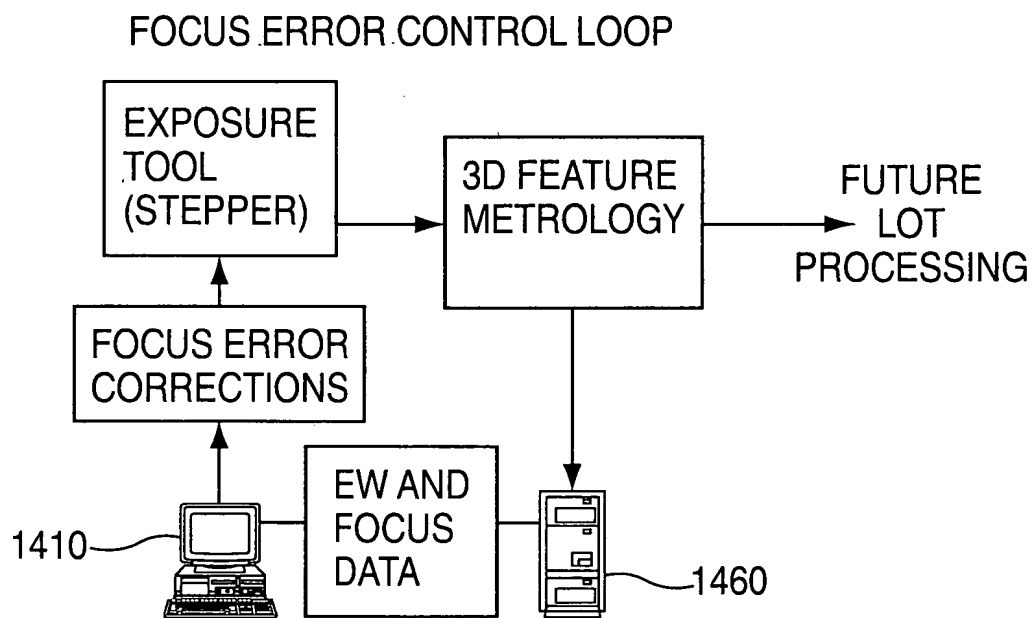


FIG. 14